

IN THE SPECIFICATION

Page 1, lines 1-2:

Title of the Invention

~~Semiconductor Device and Method for Manufacturing the Same~~

Method for Manufacturing SOI LOCOS MOSFET with Metal Oxide Film
or Impurity-Implanted Field Oxide

Paragraph starting at page 8, line 7:

In an element isolation region A, a metal oxide film 180, e.g., aluminum oxide (Al_2O_3) is formed on the silicon layer 130 having an inclined part in a sectional shape (e.g., the inclined edge of the silicon layer 130 shown within circle 135 in Fig. 2D) and on the BOX oxide film layer 120. And the field oxide film 160 is formed thereon.

Second full paragraph on page 11:

Next, in order to generate a negative fixed electric charge on the field oxide film 260 as shown in Fig. 3C, an impurity, for example, ~~[[a]]~~ fluorine ions ~~F-280 is~~ are implanted into the whole surface of the substrate by an ion implantation method, indicated by inclined arrows in Fig. 3C, after forming the field oxide film 260. At this time, it is preferable to implement at an angle of approximately 30° - 45° in order to implant the fluorine ions ~~[[280]]~~ effectively into the field oxide film 260 on the inclined silicon layer 230 in the edge region 235. It is also preferable to set the energy of implantation approximately at 10-15 keV.

Last full paragraph on page 11:

Next, in order to generate a negative fixed electric charge on the field oxide film 260 as shown in Fig. 3C, an impurity, for example, ~~[[a]] fluorine ion F-280 is~~ ions are implanted into the whole surface of the substrate by an ion implantation method after forming the field oxide film 260. At this time, it is preferable to implement at an angle of approximately 30°-45° in order to implant the fluorine ions [[280]] effectively into the field oxide film 260 on the inclined silicon layer 230 in the edge region 235 (i.e., the inclined edge of the silicon layer 230 shown within circle 235 in Fig. 3B). Fig. 3C shows that the diagonal ion implantation is directed generally perpendicular to the inclined edge of the silicon layer 230. It is also preferable to set the energy of implantation approximately at 10-15 keV.

First full paragraph on page 12:

By implanting the fluorine ions [[280]] into the field oxide film 260 at the interface of the silicon layer in the edge region 235, since a negative fixed electric charge is generated at the interface of the silicon layer 230 in the field oxide film 260, the flat band voltage of the edge region and the threshold value of the parasitic N-channel MOSFET increase.